/ Descriptions

TO-251 N MOS N-CHANNEL MOSFET in a TO-251 Plastic Package.

/ Features

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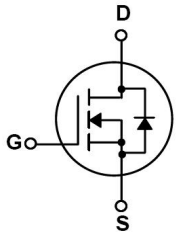
Low gate charge, low crss, fast switching.

/ Applications

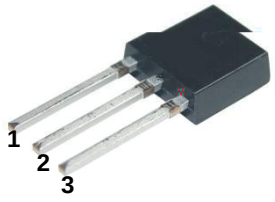
DC/DC

These devices are well suited for high efficiency switching DC/DC converters and switch mode power supplies.

/ Equivalent Circuit



/ Pinning



PIN1 G PIN 2 D PIN 3 S

/ h_{FE} Classifications & Marking

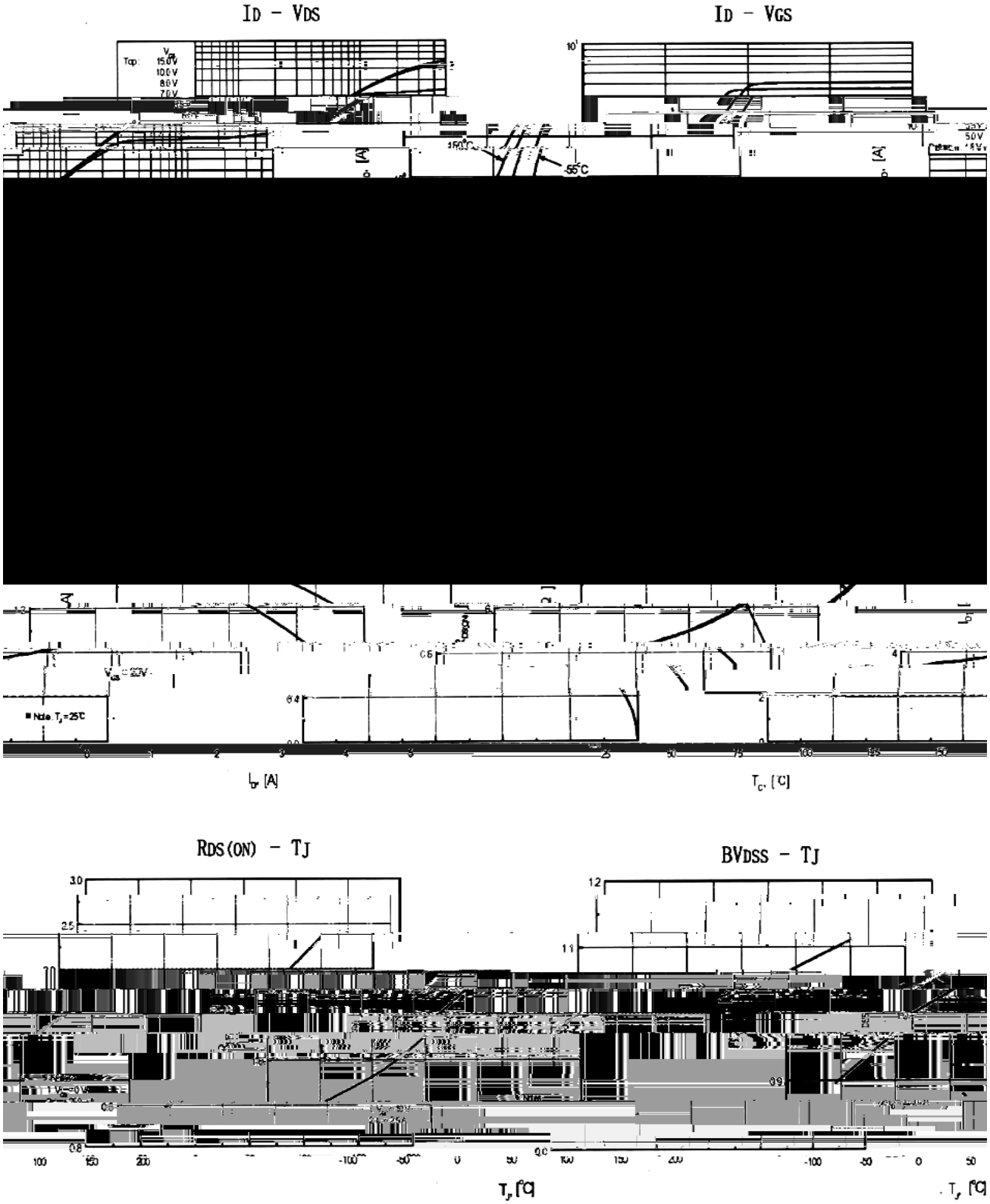
See Marking Instructions.

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DSS}	600	V
Drain Current	I_D(Tc=25)	2.0	A
Drain Current	I_D(Tc=100)	1.3	A
Drain Current - Pulsed	I_{DM}	6.0	A
Gate-Source Voltage	V_{GSS}	±30	V
Single Pulsed Avalanche Energy	E_{AS}	120	mJ
Repetitive Avalanche Energy	E_{AR}	5.4	mJ
Avalanche Current	I_{AR}	2.0	A
Power Dissipation	P_D(Tc=25)	45	W
Operating and Storage Temperature Range	T_J,T_{STG}	-55 to 150	

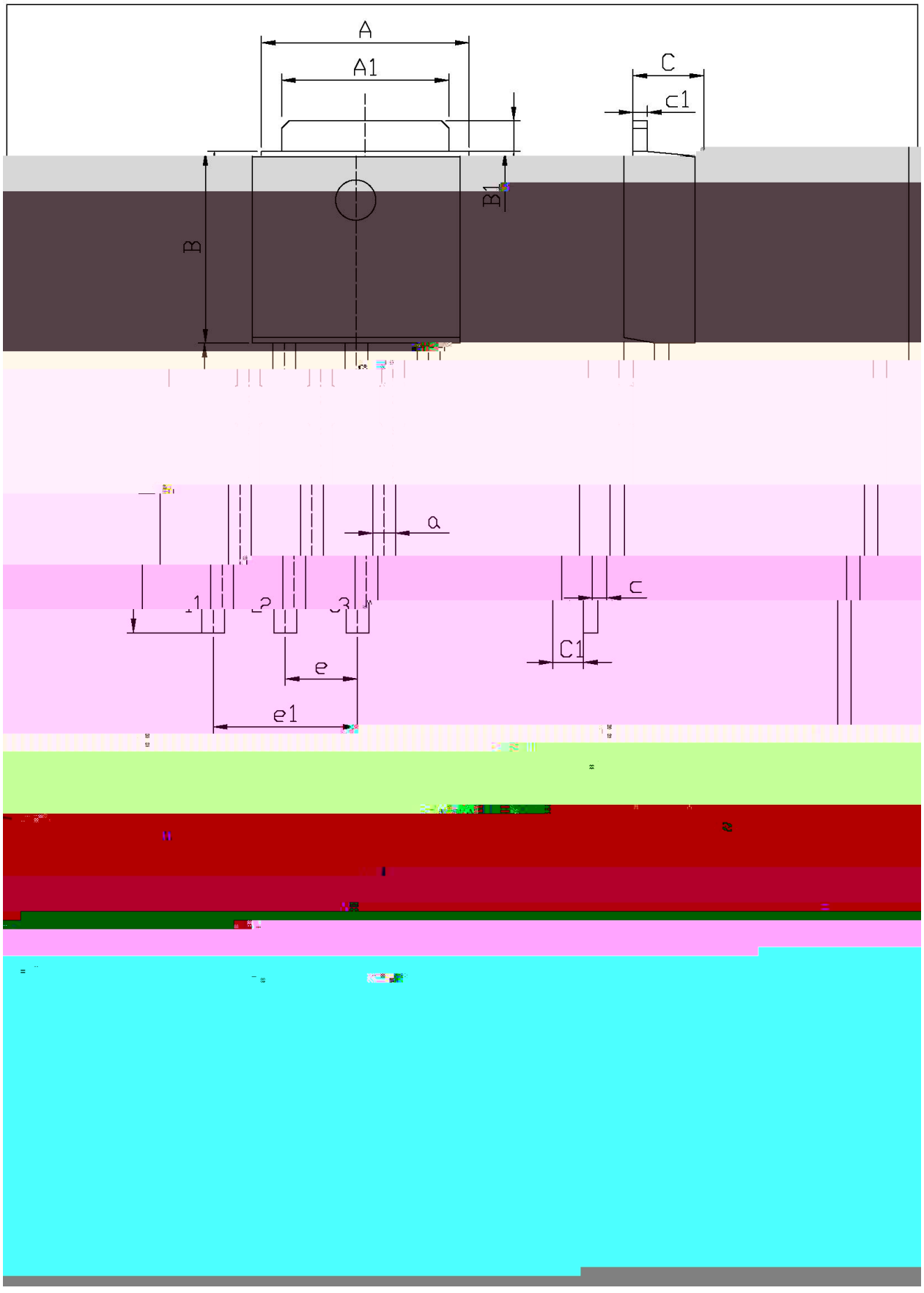
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Parameter Symbol

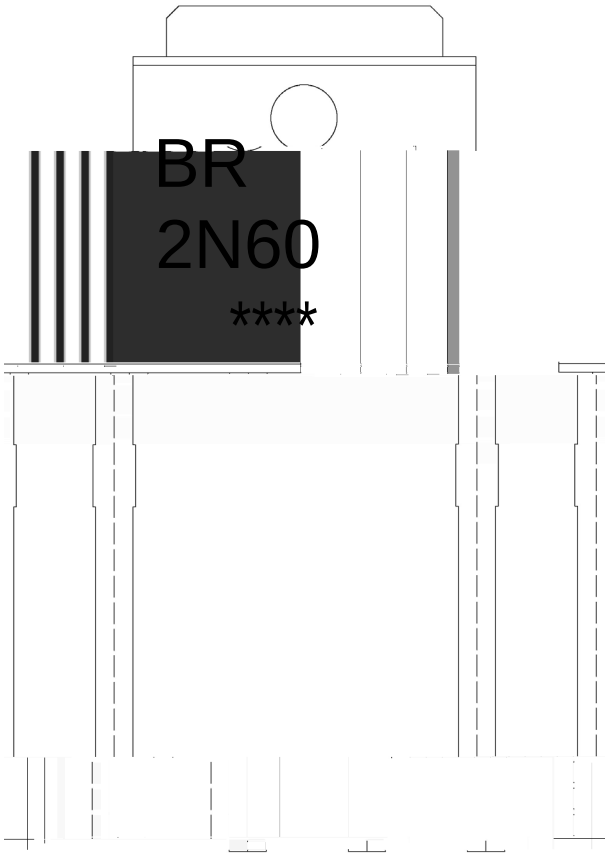
/ Electrical Characteristic Curve



/ Package Dimensions



/ Marking Instructions



BR

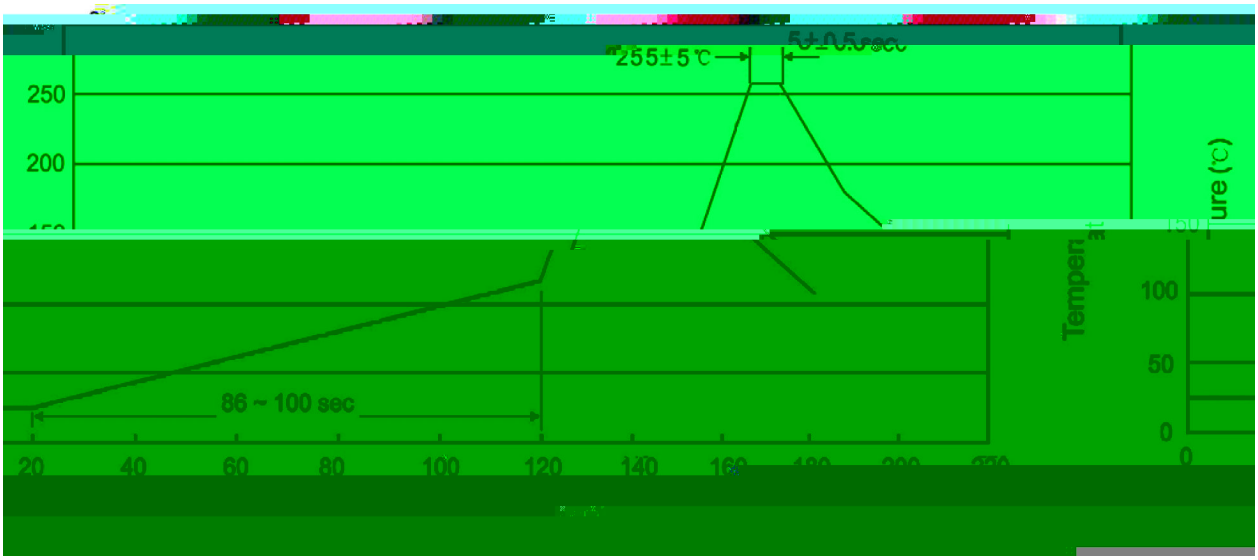
2N60

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Note:

BR:	Company Code
2N60:	Product Type.
****:	Lot No. Code, code change with Lot No.

( ) / Temperature Profile for Dip Soldering(Pb-Free)



					Note:	
1		25 150		60 90sec;	1.Preheating:25~150 , Time:60~90sec.	
2		255±5		5±0.5sec;	2.Peak Temp.:255±5 , Duration:5±0.5sec.	
3			2 10 /sec.		3. Cooling Speed: 2~10 /sec.	

/ Resistance to Soldering Heat Test Conditions

270±5	10±1 sec.	Temp.:270±5	Time:10±1 sec

/ Packaging SPEC.

/ BULK

Package Type 封装形式	Units 包装数量					Dimension 包装尺寸 (unit: mm^3)		
	Units/Bag 只/袋	Bags/Inner Box 袋/盒	Units/Inner Box 只/盒	Inner Boxes/Outer Box 盒/箱	Units/Outer Box 只/箱	Bag 袋	Inner Box 盒	Outer Box 箱
TO-251	1,000	10	10,000	5	50,000	135×190	237×172×102	560×245×195

/ TUBE

Package Type 封装形式	Units 包装数量	Dimension 包装尺寸 (unit: mm^3)
	Units/Tube 只/套管	